

Title (en)
OXYNITRIDE SPUTTERING TARGET

Title (de)
OXYNITRID-SPUTTERING-TARGET

Title (fr)
CIBLE DE PULVERISATION CATHODIQUE D'OXYNITRURE

Publication
EP 2134883 A1 20091223 (FR)

Application
EP 08788046 A 20080326

Priority
• FR 2008050520 W 20080326
• FR 0754340 A 20070406

Abstract (en)
[origin: WO2008132409A1] Sputtering target comprising: - between 30 and 40 at% of a metal, - between 2 and 10 at% nitrogen - between 35 and 50 at% oxygen, - the complement to 100% being composed of at least one element chosen from the group comprising phosphorous (P), boron (B), silicon (Si), germanium (Ge), gallium (Ga), sulphur (S) and aluminium (Al). A method of manufacturing a thin film from the target and an electrochemical device comprising the thin film.

IPC 8 full level
C23C 14/06 (2006.01); **C23C 14/35** (2006.01); **H01M 4/40** (2006.01); **H01M 10/0562** (2010.01); **H01M 10/058** (2010.01); **H01M 10/36** (2010.01); **H01M 50/403** (2021.01); **H01M 50/434** (2021.01)

CPC (source: EP KR US)
C23C 14/0036 (2013.01 - EP US); **C23C 14/06** (2013.01 - KR); **C23C 14/0641** (2013.01 - US); **C23C 14/0676** (2013.01 - EP US); **C23C 14/08** (2013.01 - US); **C23C 14/3407** (2013.01 - KR); **C23C 14/3414** (2013.01 - EP KR US); **H01J 37/3414** (2013.01 - US); **H01J 37/3426** (2013.01 - US); **H01M 6/18** (2013.01 - EP US); **H01M 6/40** (2013.01 - EP US); **H01M 10/0562** (2013.01 - EP US); **H01M 10/058** (2013.01 - EP US); **H01M 50/403** (2021.01 - EP KR US); **H01M 50/434** (2021.01 - EP KR US); **H01J 37/3411** (2013.01 - US); **H01M 2300/0068** (2013.01 - EP US); **H01M 2300/0071** (2013.01 - US); **Y02E 60/10** (2013.01 - EP US); **Y02P 70/50** (2015.11 - EP)

Citation (search report)
See references of WO 2008132409A1

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